

# Switching diode

## 1SS244

### ●Applications

High voltage switching  
General purpose rectification

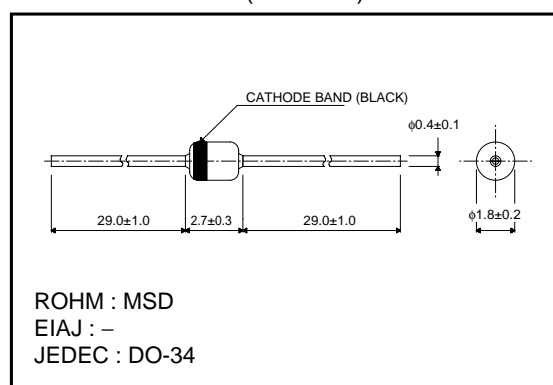
### ●Features

- 1) Glass sealed envelope. (MSD)
- 2)  $V_{RM}=250V$  guaranteed.
- 3) High reliability.

### ●Construction

Silicon epitaxial planar

### ●External dimensions (Units : mm)



### ●Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	250	V
DC reverse voltage	$V_R$	220	V
Peak forward current	$I_{FM}$	625	mA
Mean rectifying current	$I_o$	200	mA
Surge current (1s)	$I_{surge}$	1000	mA
Power dissipation	$P$	300	mW
Junction temperature	$T_j$	175	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65~+175	$^\circ\text{C}$

### ●Electrical characteristics ( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	1.5	V	$I_F=200\text{mA}$
Reverse current	$I_R$	-	-	10	$\mu\text{A}$	$V_R=220\text{V}$
Capacitance between terminals	$C_T$	-	-	3	pF	$V_R=0\text{V}$ , $f=1\text{MHz}$
Reverse recovery time	$t_{rr}$	-	-	75	ns	$I_F=20\text{mA}$ , $I_R=20\text{mA}$ , $R_L=50\Omega$

Diodes

●Electrical characteristics curves (Ta=25°C)

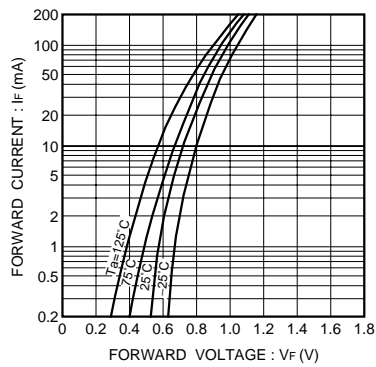


Fig.1 Forward characteristics

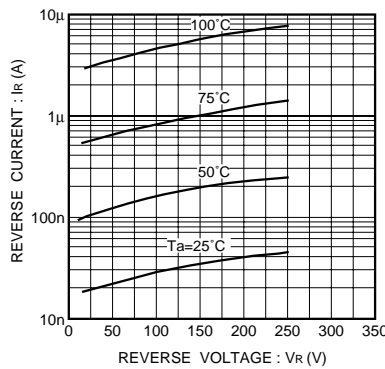


Fig.2 Reverse characteristics

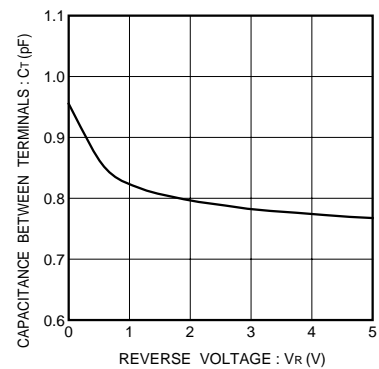


Fig.3 Capacitance between terminals characteristics

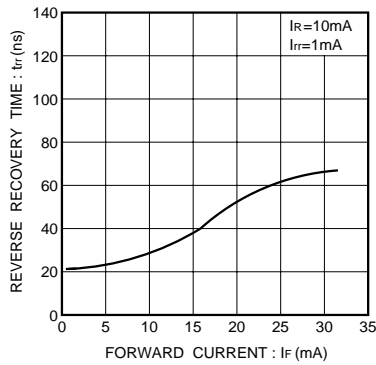


Fig.4 Reverse recovery time characteristics

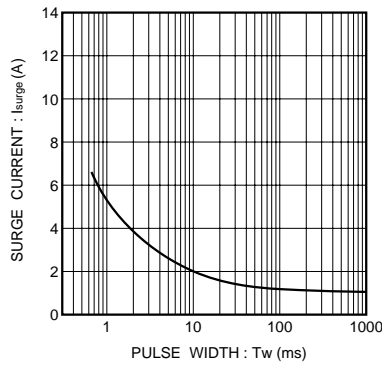


Fig.5 Surge current characteristics

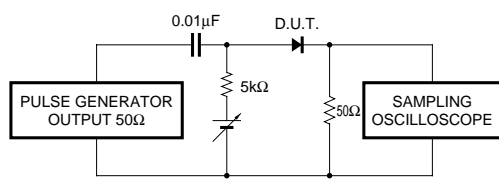


Fig.6 Reverse recovery time (trr) measurement circuit